Central™
Semiconductor Corp.

PROCESS CP315V

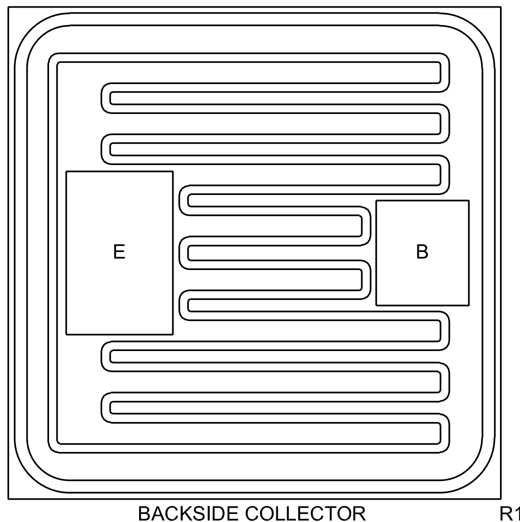
Power Transistors

NPN - High Current Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	40 X 40 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	7.9 X 8.7 MILS
Emitter Bonding Pad Area	9.0 X 14 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

Geometry



GROSS DIE PER 4 INCH WAFER

6,936

PRINCIPAL DEVICE TYPES

CXT3150
CZT3150

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R1 (26-August 2008)

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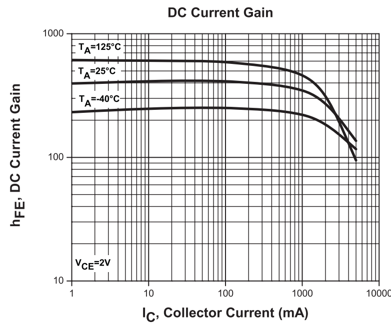
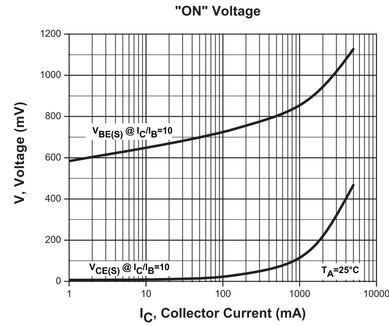
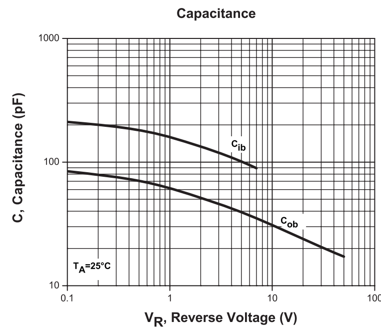
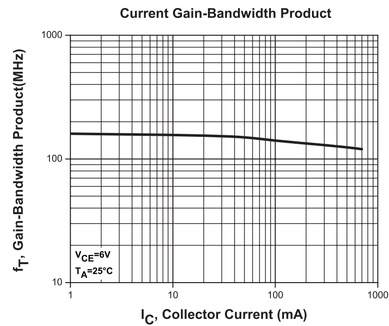
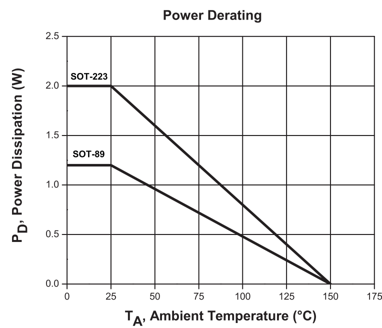
Typical Electrical Characteristics











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